

SUBSTITUTE FORM PTO-1449 (MODIFIED)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. TPS/007	SERIAL NO. Unknown	
		INFORMATION DISCLOSURE STATEMENT BY APPLICANT			APPLICANT Dip et al.		
(37 CFR 1.98(b))		(Use several sheets if necessary)			FILING DATE March 10, 2004	GROUP Unknown	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A.A						
	A.B						
	A.C						
	A.D						
	A.E						
	A.F						
	A.G						
	A.H						
	A.I						
	A.J						
	A.K						
FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS							
		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION (YES/NO)
CPM	A.L	EP0684650 B1	08/29/2001	EP	H01L	29/786	
	A.M						
	A.N						
	A.O						
	A.P						
	A.Q						
OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)							
CPM	A.R	Stephen St. Onge and Mark Dupuis, <u>Innovations in Silicon Germanium Bicmos Processing, Semiconductor Fablech - 12th Edition, pp 195-199, published July, 2000.</u>					
	A.S						
	A.T						
EXAMINER <i>Colleen Mathus</i>		DATE CONSIDERED <i>07/10/2006</i>					
EXAMINER: Initial if citation considered, whether or not in conformance. Draw line through citation only if not in conformance <u>and</u> not considered. Include a copy of this form with next communication to Applicant.							

SUBSTITUTE FORM PTO-1449 (MODIFIED)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE							ATTY. DOCKET NO. TPS-007	SERIAL NO. 10/797,876
AUG 11 2005 (37 CFR 1.98(b))		INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use several sheets if necessary)</i>							APPLICANT Anthony Dip et al.	
									FILING DATE March 10, 2004	GROUP 2813

U.S. PATENT DOCUMENTS													
EXAMINER INITIAL		PATENT NUMBER						ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
CAM	A.A	5	2	5	9	8	8	1	11/09/1993	Edwards et al.	118	719	05/17/1991
CAM	A.B	6	2	9	6	7	1	1	10/02/2001	Loan et al.	118	726	10/20/1999
CAM	A.C	6	4	8	8	7	7	7	12/03/2002	Madan et al.	118	718	04/03/2001
	A.D												
	A.E												
	A.F												
	A.G												
	A.H												
	A.I												
	A.J												
	A.K												

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	A.L						
	A.M						
	A.N						
	A.O						
	A.P						
	A.Q						

OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)						
EXAMINER	DATE CONSIDERED					
CAM	A.R	Cho et al., <u>Interfacial Characteristics of HfO_x Films Grown on Strained Si_{1-x}Ge_x by Atomic-Layer Deposition</u> , Applied Physics Letters, Vol. 84, No. 7, 02/16/2004, pp. 1171-1173				
CAM	A.S	J. Westlinder et al., <u>Effects of Low-Temperature Water Vapor Annealing of Strained SiGe Surface-Channel pMOSFETs with High-k Dielectric</u> , European Solid-State Device Research, 09/16/2003, pp. 525-528				
CAM	A.T	S. Pal et al., <u>Gd₂O₃, Ga₂O₃(Gd₂O₃), Y₂O₃, and Ga₂O₃ as High-k Gate Dielectrics on SiGe: A Comparative Study</u> , J. Applied Physics, Vol. 90, No. 8, 10/15/2001, pp. 4103-4107				
Colleen Mathews	07/10/2006					

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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	B.A						
	B.B						
	B.C						
	B.D						
	B.E						
	B.F						
	B.G						
	B.H						
	B.I						
	B.J						
	B.K						

FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS							
		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION (YES/NO)
	B.L						
	B.M						
	B.N						
	B.O						
	B.P						
	B.Q						

OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)						
CAM	B.R	Choi et al., Electrical Characteristics of ZrO _x Gate Dielectric Deposited on Ultrathin Silicon Capping Layer for SiGe Metal-Oxide-Semiconductor Device Applications, Jpn. J. Appl. Physics, Part 1, Vol 41, No. 8, Aug 2002, pp. 5129-5130				
CAM	B.S	Chatterjee et al., Electrical Properties of Stacked Gate Dielectric (SiO ₂ /ZrO _x) Deposited on Strained SiGe Layers, Thin Solid Films, Vol. 422, No. 1-2, 12/20/2002, pp. 33-38				
CAM	B.T	European Patent Office, International Search Report, PCT/US2005/000661, Dated 7/27/2005, 5 pp.				

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Colleen Mattius	07/10/2006		

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